

Serial No.: 10/824,942
Examiner: Mohammad Timor Karimy
Title: SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE
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Amendments to the Claims:

This listing of claims will replace all prior versions, and listing, of claims in the application.

1. (Currently amended) A semiconductor integrated circuit device, comprising a digital circuit part and an analog circuit part that are disposed on a surface of one semiconductor substrate,

wherein a dummy layer part made of polysilicon that is the same as polysilicon composing a gate of a transistor is disposed directly on a portion of the semiconductor substrate being of higher resistance than a well region in the circuit parts of the semiconductor substrate between the digital circuit part and the analog circuit part.

2. (Currently amended) The semiconductor integrated circuit device according to claim 1,

wherein a dummy diffused region ~~further~~ is further provided between the dummy layer part and one of the digital circuit part and the analog circuit part, and a power-supply potential is applied to the dummy diffused region.

3. (Original) The semiconductor integrated circuit device according to claim 1, wherein the digital circuit part is a circuit for driving a sensor array, and the analog circuit part is a circuit for analog processing an image detecting signal that is output from the sensor array.

4. (Original) The semiconductor integrated circuit device according to claim 3, wherein the sensor array is a CCD area sensor, a CCD linear sensor or a CMOS sensor.

5. (Currently amended) A camera, comprising:
an imaging element; and

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a semiconductor integrated circuit device comprising a digital circuit part for driving the imaging element and an analog circuit part for analog processing an image detecting signal output from the imaging element,

wherein the semiconductor integrated circuit device has a structure in which a dummy layer part made of polysilicon that is the same as polysilicon composing a gate of a transistor is disposed directly on a portion of the semiconductor substrate being of higher resistance than a well region in the circuit part of the semiconductor substrate between the digital circuit part and the analog circuit part.

6. (New) The camera according to claim 5,
wherein a dummy diffused region is further provided between the dummy layer part and one of the digital circuit part and the analog circuit part, and
a power-supply potential is applied to the dummy diffused region.